

LASER DIODE, SEMICONDUCTOR LIGHT-EMITTING DEVICE, AND  
METHOD OF PRODUCTION THEREOF

ABSTRACT OF THE DISCLOSURE

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10 A laser diode capable of reducing an operating  
current and thereby improving long term reliability and  
able to be produced by a simpler process than in the  
prior art and a semiconductor light emitting device and a  
method of production thereof; wherein a first clad layer,  
an active layer, and a second clad layer are formed on a  
substrate, a third clad layer and a contact layer are  
formed on a current injection stripe region thereon, an  
15 electrode is formed so as to be connected to the second  
clad layer in regions other than the current injection  
stripe region and to be connected to the contact layer,  
and, at the time of emitting laser light from a laser  
light oscillation region by injection of a first current  
20 to the electrode via the contact layer by application of  
voltage, a second current which is smaller than the first  
current is injected in regions other than the current  
injection stripe region via the second clad layer, so  
that a laser diode is configured wherein currents at ends  
25 of the laser light oscillation region are controlled to

